

Schottky barrier diode

RB471E

●Applications

Low current rectification
For switching power supplies

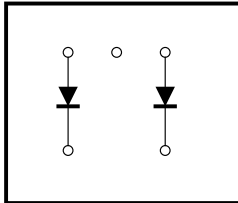
●Features

- 1) Small surface mounting dual element parallel type.
(SMD5)
- 2) Low V_F . ($V_F=0.45V$ Typ. at 100mA)
- 3) High reliability.

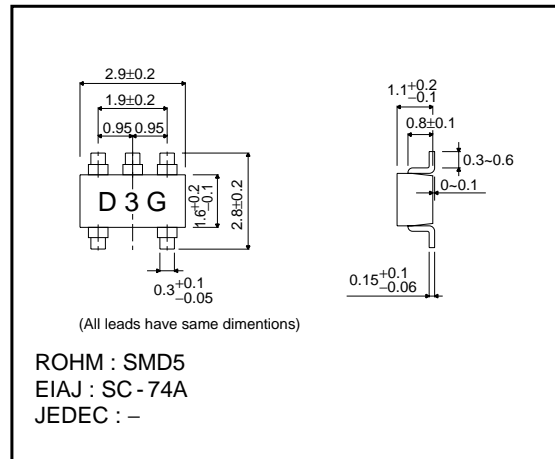
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40~+125	$^\circ C$

* 60 Hz for 1 μs

Diodes

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{F1}	—	0.28	0.34	V	I _F =10mA
	V _{F2}	—	0.45	0.55	V	I _F =100mA
Reverse current	I _R	—	1	30	μA	V _R =10V
Capacitance between terminals	C _T	—	6.0	—	pF	V _R =10V, f=1MHz

Note) ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

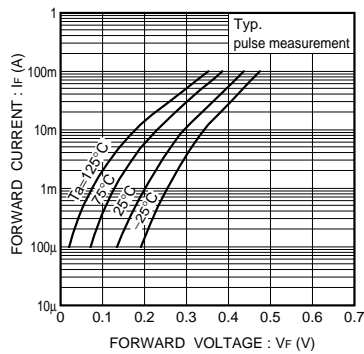


Fig. 1 Forward characteristics

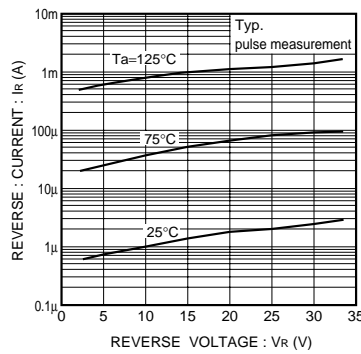


Fig. 2 Reverse characteristics

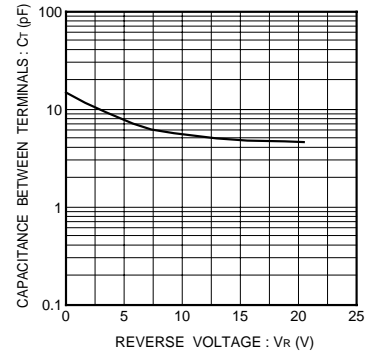


Fig. 3 Capacitance between terminals characteristics

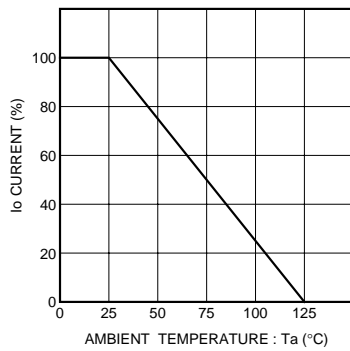


Fig 4. Derating curve (mounting on glass epoxy PCBs)